

## IN THE CLAIMS

Claims 1-7 (canceled) (restriction)

8. (original) An integrated circuit comprising:

a plurality of transistors having a principal operating voltage;

a deep n well comprising n- material, wherein a portion of said deep n well is coupled to p type material which is coupled to a ground reference of said integrated circuit; and

wherein said deep n well is coupled to said principal operating voltage of said plurality of transistors of said integrated circuit.

9. (original) The integrated circuit of Claim 8 wherein said deep n well is substantially surrounded by p type material.

10. (original) The integrated circuit of Claim 8 wherein said deep n well comprises a substantially circular cross section.

11. (original) The integrated circuit of Claim 8 comprising a plurality of said deep n wells.

12. (original) The integrated circuit of Claim 8 wherein said deep n well is parasitically coupled to said principal operating voltage.

13. (original) The integrated circuit of Claim 8 wherein said p type material comprises epitaxy.

14. (original) The integrated circuit of Claim 8 wherein said p type material comprises bulk p material.

15. (original) The integrated circuit of Claim 8 wherein said p type material comprises a p well.

16. (original) The integrated circuit of Claim 15 wherein said p well is at substantially a same depth as said deep n well.

Claims 17-31 (canceled) (restriction)